

International **IR** Rectifier

HEXFRED™

PD - 20368

HFA45HC60C

Ultrafast, Soft Recovery Diode

Features

- Reduced RFI and EMI
- Reduced Snubbing
- Extensive Characterization of Recovery Parameters
- Hermetic

$V_R = 600V$

$I_{F(AV)} = 45A$

$t_{fr} = 37ns$

Description

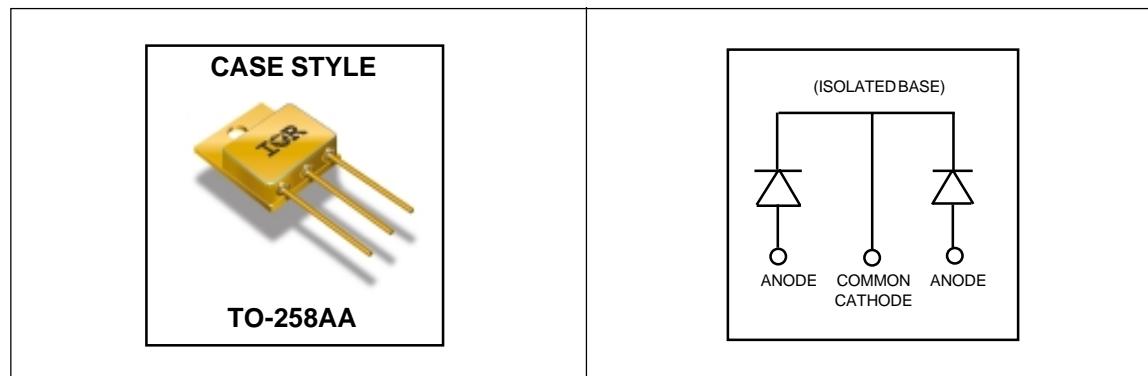
HEXFRED™ diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and di/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

Absolute Maximum Ratings

| | Parameter | Max. | Units |
|--------------------------|--|-------------|-------|
| V_R | Cathode to Anode Voltage | 600 | V |
| $I_{F(AV)}$ | Continuous Forward Current, ① $T_C = 80^\circ C$ | 45 | A |
| I_{FSM} | Single Pulse Forward Current, ② $T_C = 25^\circ C$ | 225 | |
| $P_D @ T_C = 25^\circ C$ | Maximum Power Dissipation | 104 | W |
| T_J, T_{STG} | Operating Junction and Storage Temperature Range | -55 to +150 | °C |

Note: ① D.C. = 50% rect. wave

② 1/2 sine wave, 60 Hz , P.W. = 8.33 ms



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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Test Conditions | |
|---------------------|----------------------------------|------|------|------|---------------|---|--|
| V_{BR} | Cathode Anode Breakdown Voltage | 600 | — | — | V | $I_R = 100\mu\text{A}$ | |
| V_F See Fig. 1 | Forward Voltage | — | — | 1.37 | V | $I_F = 22.5\text{A}, T_J = -55^\circ\text{C}$ | |
| | | — | — | 1.47 | | $I_F = 22.5\text{A}, T_J = 25^\circ\text{C}$ | |
| | | — | — | 1.81 | | $I_F = 45\text{A}, T_J = 25^\circ\text{C}$ | |
| | | — | — | 1.37 | | $I_F = 22.5\text{A}, T_J = 125^\circ\text{C}$ | |
| I_R See Fig. 2 | Reverse Leakage Current | — | — | 10 | μA | $V_R = V_R \text{ Rated}$ | |
| | | — | — | 1.0 | mA | $V_R = V_R \text{ Rated}, T_J = 125^\circ\text{C}$ | |
| C_T | Junction Capacitance, See Fig. 3 | — | — | 65 | pF | $V_R = 200\text{V}$ | |
| L_S | Series Inductance | — | 8.7 | — | nH | Measured from anode lead to cathode lead , 6mm (0.025 in) from package | |

Dynamic Recovery Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Test Conditions | |
|--------------------|---|------|------|------|------------------|--|--|
| t_{rr} | Reverse Recovery Time | — | — | 37 | ns | $I_F = 1.0\text{A}, V_R = 30\text{V}, di/dt = 200\text{A}/\mu\text{s}$ | |
| t_{rr1} | Reverse Recovery Time | — | 74 | — | ns | $T_J = 25^\circ\text{C}$ See Fig. | |
| t_{rr2} | | — | 194 | — | | $T_J = 125^\circ\text{C}$ 5 | |
| I_{RRM1} | Peak Recovery Current | — | 7.5 | — | A | $T_J = 25^\circ\text{C}$ See Fig. | |
| I_{RRM2} | | — | 12 | — | | $T_J = 125^\circ\text{C}$ 6 | |
| Q_{rr1} | Reverse Recovery Charge | — | 270 | — | nC | $T_J = 25^\circ\text{C}$ See Fig. | |
| Q_{rr2} | | — | 1210 | — | | $T_J = 125^\circ\text{C}$ 7 | |
| $di_{(rec)M}/dt_1$ | Peak Rate of Fall of Recovery Current During t_b | — | 400 | — | A/ μs | $T_J = 25^\circ\text{C}$ See Fig. | |
| $di_{(rec)M}/dt_2$ | | — | 100 | — | | $T_J = 125^\circ\text{C}$ 8 | |

Thermal - Mechanical Characteristics

| | Parameter | Typ. | Max. | Units |
|------------|------------------|------|------|---------------------------|
| R_{thJC} | Junction-to-Case | — | 1.2 | $^\circ\text{C}/\text{W}$ |
| Wt | Weight | 10.9 | — | g |

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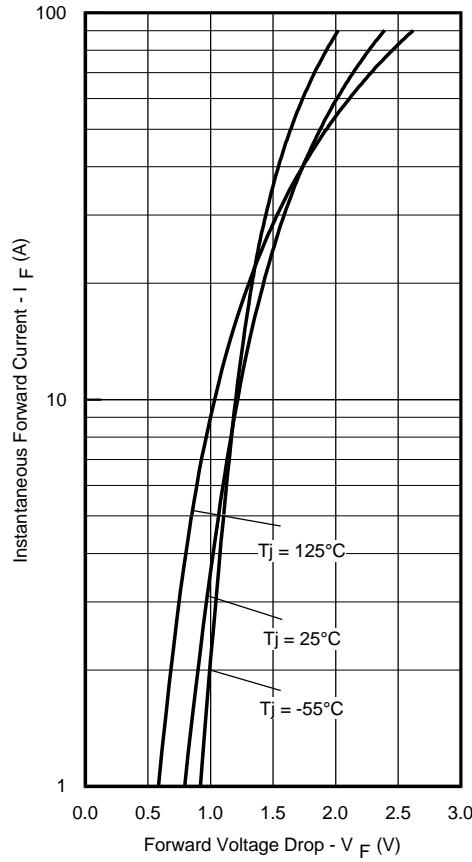


Fig. 1 - Maximum Forward Voltage Drop Vs.
Instantaneous Forward Current

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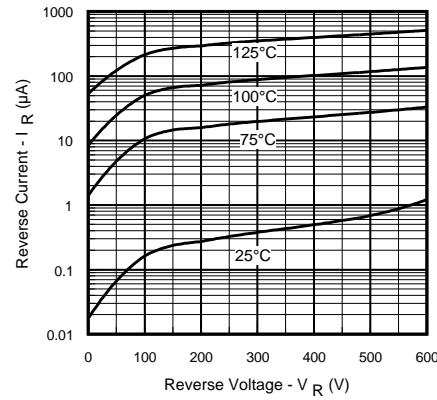


Fig. 2 - Typical Reverse Current Vs. Reverse
Voltage

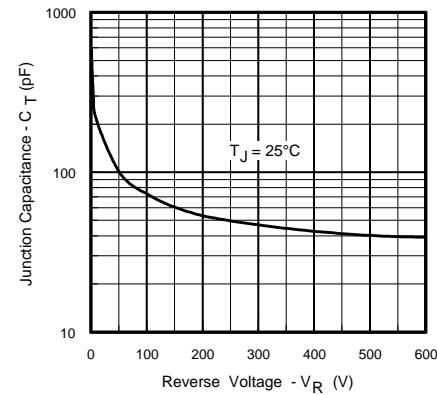


Fig. 3 - Typical Junction Capacitance Vs.
Reverse Voltage

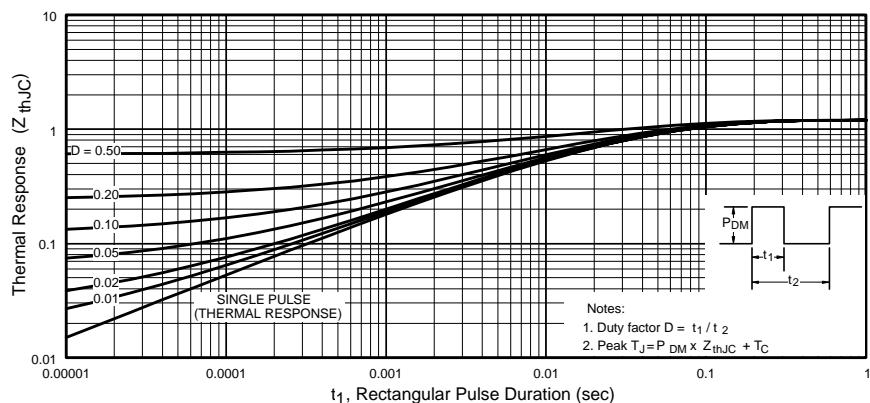


Fig. 4 - Maximum Thermal Impedance Z_{thjc} Characteristics

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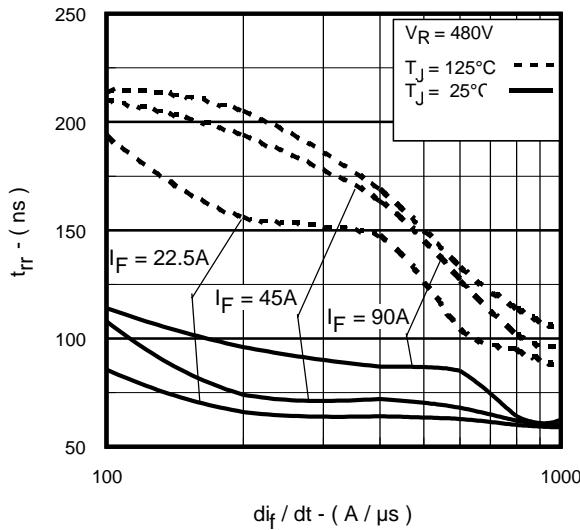


Fig. 5 - Typical Reverse Recovery Vs. di_f/dt ,

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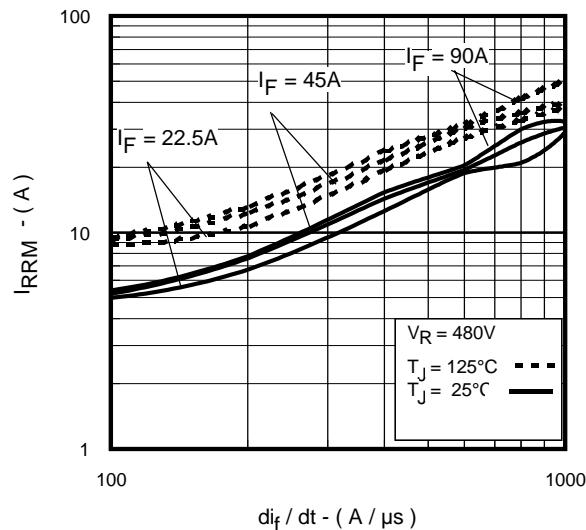


Fig. 6 - Typical Recovery Current Vs. di_f/dt ,

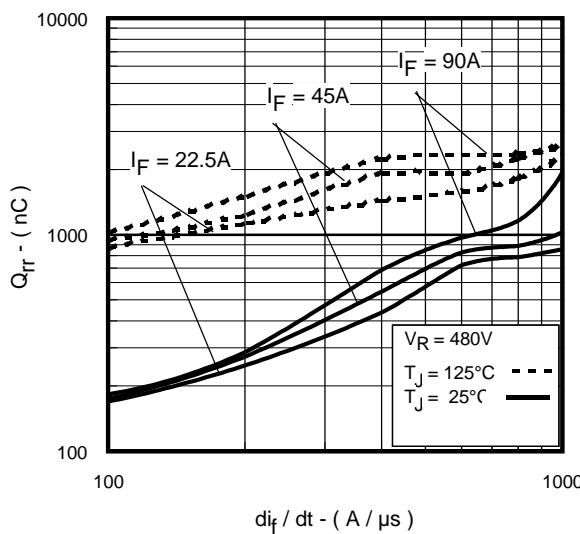


Fig. 7 - Typical Stored Charge Vs. di_f/dt

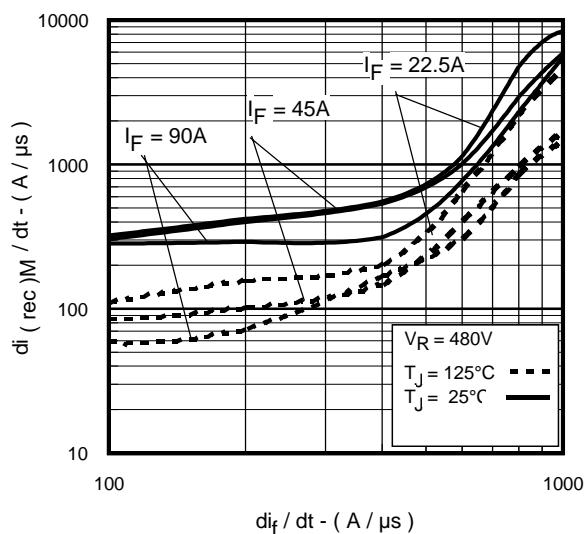


Fig. 8 - Typical $d_i_{(rec)M}/dt$ Vs. di_f/dt

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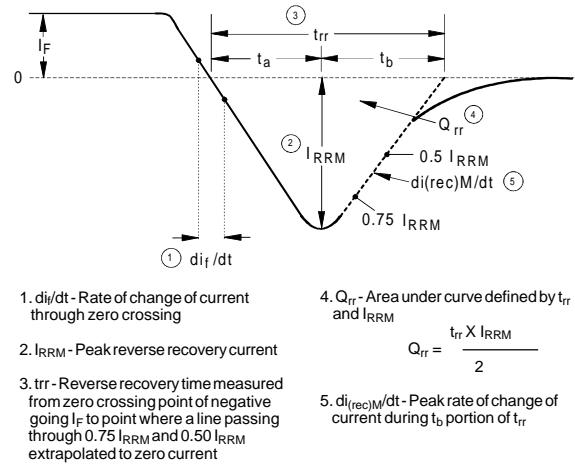
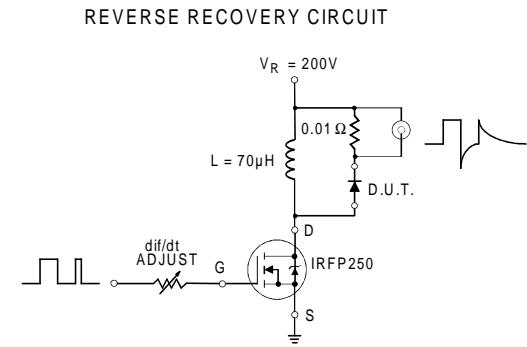
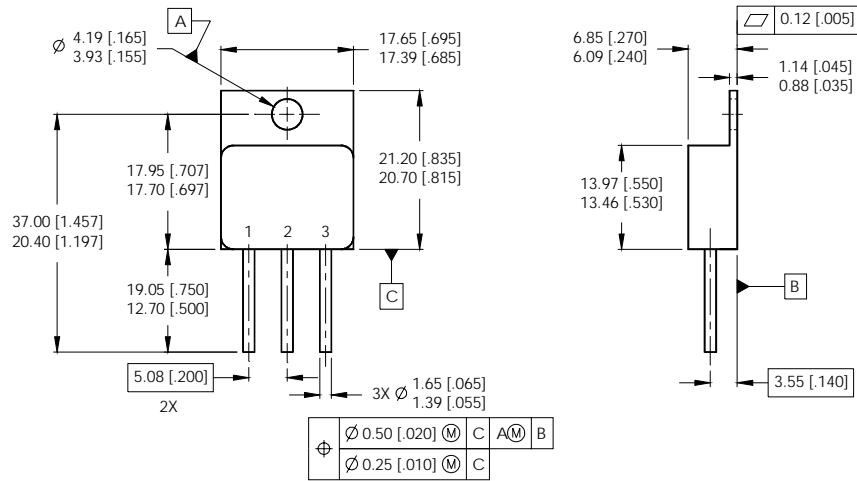


Fig. 9 - Reverse Recovery Parameter Test Circuit

Fig. 10 - Reverse Recovery Waveform and Definitions

Case Outline and Dimensions — TO-258AA



IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information.
Data and specifications subject to change without notice. 04/01